CLAIMS

1. A polishing composition used in polishing a polishing object having a barrier layer, a metal wiring layer and an insulating film, the polishing composition comprising:

abrasive grains;

an oxidant;

a metal corrosion inhibitor;

a pH adjusting agent; and

water, wherein

an aspect ratio of the abrasive grains is 1.22 or less and more than 1.0,

a ratio D90/D10 of a diameter D90 of particles when a cumulative particle weight from a fine particle side reaches 90% of a total particle weight to a diameter D10 of particles when the cumulative particle weight from the fine particle side reaches 10% of the total particle weight of the entire particles is 1.5 or more and 3.0 or less in a particle size distribution of the abrasive grains determined by a laser diffraction scattering method.

2. The polishing composition according to claim 1, wherein the abrasive grains are colloidal silica.

3. The polishing composition according to claim 1, wherein an average primary particle size of the abrasive grains is from 20 nm to 200 nm.

4. The polishing composition according to claim 1, wherein the barrier layer contains tantalum or a noble metal.

5. A polishing method to polish a polishing object having a barrier layer, a metal wiring layer and an insulating film using the polishing composition according to claim 1.

6. A method for producing a substrate, comprising:
a step of polishing a polishing object having a barrier layer, a metal wiring layer and an insulating film by the polishing method according to claim **5**.